



Features

- Low RDS(ON)
- Fast switching
- Green Device Available

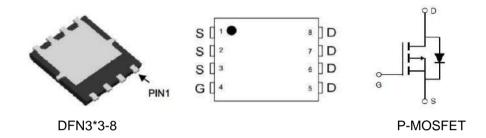
Application

- MB / VGA / Vcore
- POL Applications

Product Summary



V _{DSS}	-30	V
R _{DS(ON)-Typ.}	15	mΩ
I _D	-30	Α



Absolute Maximum Ratings (T_J=25°C Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit	
VDSS	Drain-Source Voltage		-30	W	
V _{GSS}	Gate-Source Voltage		±20	V	
TJ	Maximum Junction Temperature		150	℃	
Тѕтс	Storage Temperature Range		-55 to 150	°C	
Is	Diode Continuous Forward Current		-30	Α	
I _{DM} ^①	Pulse Drain Current Tested Tc=29		-60	Α	
Ιp	Continuous Drain Current	Continuous Prain Current	Tc=25°C	-30	Α
טו		Tc=100°C	-19		
P_D	Maximum Power Dissipation	Tc=25°C	17	W	

Thermal Characteristics

Symbol	Parameter		Rating	Unit
Rejc	Thermal Resistance-Junction to Case	Steady State	4.6	°C/W
R ₀ JA	Thermal Resistance-Junction to Ambient	Steady State	62	°C/W

Note ①: Max. current is limited by bonding wire

Note ②: UIS tested and pulse width are limited by maximum junction temperature 150°C

Note ③: Surface Mounted on 1in² FR-4 board with 1oz.



Electrical Characteristics (T_J=25°C Unless Otherwise Noted)

Parameter	Symbol	Condition	Min.	Тур	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =-250uA	-30			٧
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =-250uA	-1.2		-2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1,0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±12V ,V _{DS} =0V			±100	nA
Static Drain-source On		V _{GS} =-10V, I _D =-9A		15	20	mΩ
Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-8A		25	32	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-5A		9		s

Electronic Characteristics

Parameter	Symbol	Condition	Min.	Тур	Max.	Unit
Input capacitance	Ciss		-	1650	121	
Output capacitance	Coss	f = 1MHz	-	330	100	pF
Reverse transfer capacitance	Crss		-	220	-	

•Gate Charge characteristics(Ta = 25°C)

Parameter	Symbol	Condition	Min.	Тур	Max.	Unit
Total gate charge	Qg	VDD =25V	-	15	-	
Gate - Source charge	Qgs	ID = 8A	-	4	-	nC
Gate - Drain charge	Qgd	VGS = 10V	-	6	_	

Note: ① Pulse Test : Pulse width ≤ 300µs, Duty cycle ≤ 2%;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;



Fig.1 Power Dissipation Derating Curve

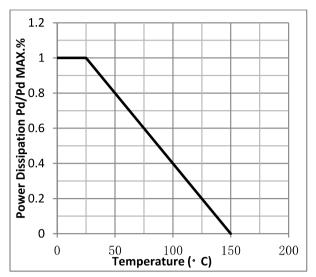


Fig.2 Typical output Characteristics

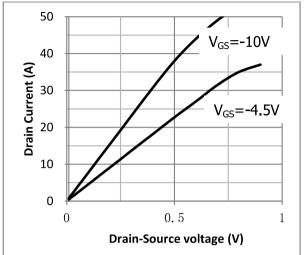


Fig.3 Threshold Voltage V.S Junction Temperature Fig.

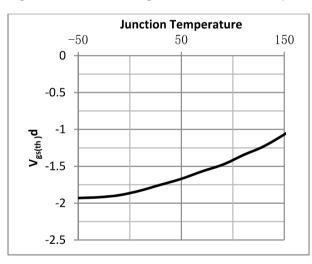


Fig.4 Resistance V.S Drain Current

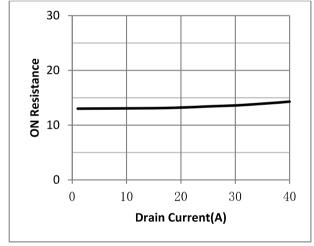


Fig.5 On-Resistance VS Gate Source Voltage

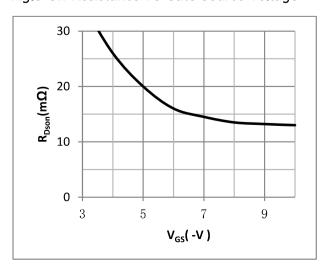


Fig.6 On-Resistance V.S Junction Temperature

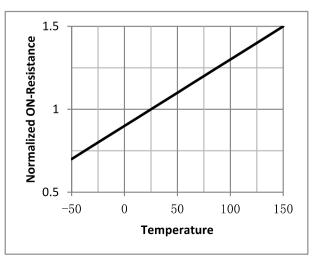




Fig.7 Switching Time Measurement Circuit

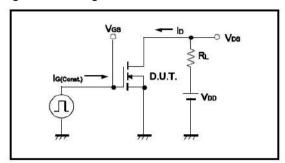


Fig.8 Gate Charge Waveform

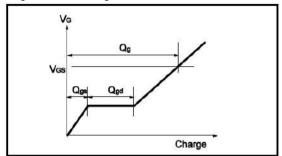


Fig.9 Switching Time Measurement Circuit

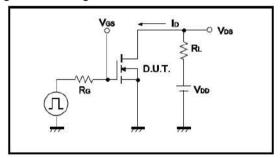


Fig.10 Gate Charge Waveform

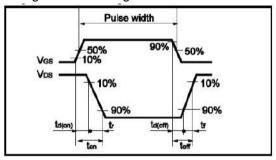


Fig.11 Avalanche Measurement Circuit

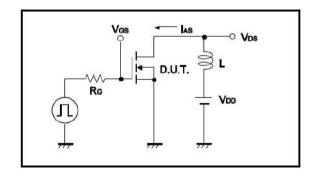
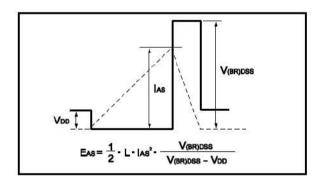


Fig.12 Avalanche Waveform



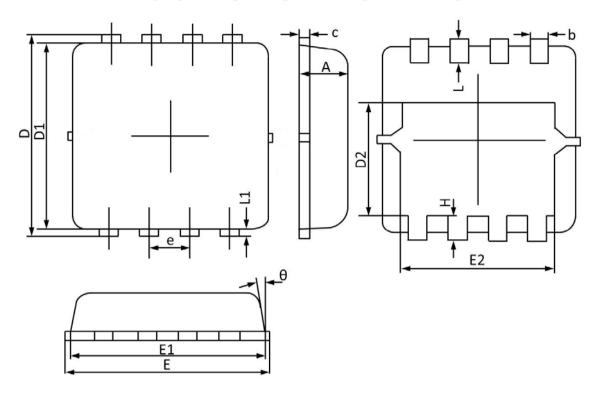


Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity
ASDM30P30CTD-R	30P30C	DFN3*3-8	Tape Reel	5000

PACKAGE	MARKING
DFN3*3-8	A5 30P30C Date Code

DFN3x3 PACKAGE INFORMATION



Symbol	Dimensions I	n Millimeters	Dimension	s In Inches
Symbol	MAX	MIN	MAX	MIN
A	0.900	0.700	0.035	0.028
b	0.350	0.240	0.014	0.009
c	0.250	0.100	0.010	0.004
D	3.450	3.050	0.136	0.120
D1	3.200	2.900	0.126	0.114
D2	1.850	1.350	0.073	0.053
E	3.400	3.000	0.134	0.118
E1	3.250	2.900	0.128	0.114
E2	2.600	2.350	0.102	0.093
e	0.65BSC		0.026BSC	
Н	0.500	0.300	0.020	0.012
L	0.500	0.300	0.020	0.012
L1	0.200	0.070	0.008	0.003
θ	12°	0°	12°	0°



ASDM30P30CTD

-30V P-Channel MOSFET

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